

Q.2a. What is epitaxial layer? Describe one way which it can be created.

Ans. Text book –II, Article 1.5.2

b. Describe the methods used to fabricate capacitors in monolithic integrated circuits.

Ans. Text book –II, Article 1.4.4

c. It is desired to fabricate a 1.5 k Ω resistors using a diffused P Layer having sheet resistance 200 Ω /squares. (4)

(i) What aspect ratio should the resistor have?

(ii) What should be the total length of the diffused region?

c)

$$\text{Resistance } R = (\rho/t)(l/W) = R_s \times a$$

Where ρ is the resistivity

$$\text{So } a = R/R_s = 1500/200 = 7.5$$

Aspect ratio = a

$$a = l/W = 7.5$$

$$l = 7.5 W = 7.5(30 \text{ micron}) = 225 \text{ micron} = 0.225 \text{ mm}$$

.3 a. In an NPN silicon transistor $\alpha = 0.995$, $I_E = 10 \text{ mA}$, leakage current $I_{CBO} = 0.5 \mu\text{A}$. Determine I_C , I_B , β , I_{CEO}

Q 3 a)

i) $I_C = \alpha I_E + I_{CBO}$

$$= 0.995 \times 10 \text{ mA} + 0.5 \mu\text{A}$$

$$= 9.9505 \text{ mA}$$

$$I_B = I_E - I_C$$

$$= 10 - 9.9505 = 49.5 \mu\text{A}$$

$$\beta = \alpha / (1 - \alpha) = .995 / (1 - .995)$$

$$= 199$$

$$I_C = \beta I_B + I_{CEO}$$

$$I_{CEO} = 9.9505 - 199 \times 0.0495 = 100 \mu\text{A}$$

b. Draw an h-parameter equivalent circuit for the CE circuit with voltage divider bias, a bypassed emitter resistor, a capacitor coupled signal source and capacitor coupled load. Briefly explain.

Ans. Text book –I , Article 6.4

Q.4a. Explain the operating Principle of N channel JFET.

Ans. Text book –I , Article 9.1

b. Explain how an FET can be used as an Amplifier?

Ans. Text book –I , Article 9.4

c. An N channel JFET has a pinch-off voltage of -4.5 V and $I_{DSS} = 9 \text{ mA}$ (8)

(i) At what value of V_{GS} in the pinch-off region will $I_D = 3 \text{ mA}$

(ii) What is the value of $V_{DS(sat)}$ when $I_D = 3 \text{ mA}$

$$c) i) I_D = I_{DSS} (1 - V_{GS}/V_P)^2$$

$$V_{GS} = V_P (1 - \sqrt{I_D / I_{DSS}})$$

$$= -1.9V$$

$$ii) I_D = I_{DSS} (V_{DS(sat)}/V_P)^2$$

$$= V_{DS(sat)} = \sqrt{(V_P)^2 I_D / I_{DSS}}$$

$$= (4.5)^2 (3 \text{ mA}) / (9 \text{ mA}) = 2.6V$$

Q.5 a. Explain how LED different from an ordinary pn junction diode? Describe its construction in brief.

Ans. Text book –I , Article 20.2

b. Two amplifier stages are required to be coupled by a coupling transformer, if the output impedance of first stage is 12 kΩ while the input impedance of the second stage is 3 kΩ. What should be the inductance of primary and secondary of the transformer so that perfect matching be obtained at a frequency of 250 Hz.

b) b) Operating frequency= $f = 250 \text{ Hz}$

output impedance of first stage= $12 \text{ k}\Omega$

input impedance of second stage= $3 \text{ k}\Omega$

Let the inductance of primary winding = L_p

Primary impedance = $2 \pi f L_p$

For perfect impedance matching= $12000 = 2 \pi f L_p$

$$L_p = 7.64 \text{ H}$$

Let the inductance of secondary winding= L_s

Secondary inductance= $2 \pi f L_s$

For perfect impedance matching=

$$3000 = 2 \pi f L_s$$

$$L_s = 1.91 \text{ H}$$

2x4 = 8 marks

Q.6 a. What are the characteristics of ideal OPAMP?

Ans. Text book –II , Article 2.3

b. Define the following parameters:

(4)

- (i) Input bias current
- (ii) CMMR
- (iii) Slew Rate
- (iv) Input offset voltage

Ans. Text book –II , Article 2.37, 3.22

c. When the inputs to a certain differential amplifier are $v_{i1} = 0.1 \sin\phi t$ and $v_{i2} = -0.1 \sin\phi t$. It is found that outputs are $v_{o1} = -5 \sin\phi t$ and $v_{o2} = 5 \sin\phi t$. When both inputs are $2 \sin\phi t$, the outputs are $v_{o1} = -0.05 \sin\phi t$ and $v_{o2} = 0.05 \sin\phi t$. Find the CMMR in dB.

$$c) A_d = \frac{V_{o1} - V_{o2}}{V_{i1} - V_{i2}} = \frac{-5 - 5}{0.1 - (-0.1)}$$

$$= -50$$

$$A_{cm} = \frac{(V_{o1} - V_{o2})_{cm}}{V_{cm}}$$

$$= \frac{-0.05 - 0.05}{2} = -0.05$$

$$CMMR = \frac{|A_d|}{|A_{cm}|} = \frac{50}{0.05} = 1000$$

$$CMMR = 20 \log_{10}(1000) = 60 \text{ dB Ans} \quad 6 \text{ marks}$$

Q.7 a. Draw and explain the working of OPAMP integrator. Draw input and output waveforms of the circuit.

Ans. Text book –I , Article 4.3

b. Design a practical differentiator that will differentiate signals with frequencies upto 200 Hz. The gain at 10 Hz should be 0.1

b) Select R_1 and C to produce break frequency f_b that is well above $f_h = 200 \text{ Hz}$. Let us choose $f_b = 10$
 $f_h = 2 \text{ kHz}$, letting $C = 0.1 \mu\text{F}$

$$f_b = 1/2\pi R_1 C \text{ Hz} =$$

$$R_1 = 1/2\pi(2 \times 10^3)(10^{-7}) = 796 \Omega$$

In order to achieve a gain of 0.1 at 10 Hz

$$\text{Gain} = A_w R_f C / A$$

$$= 0.1 = \omega R_f C = (2\pi \times 10) R_f (10^{-7}) =$$

$$R_f = 15.9 \text{ k}\Omega$$

Q.8 a. What are the applications of Schmit Trigger? Explain the operation of Schmit Trigger.

Ans. Text book –II , Article 5.3

b. Draw the circuit of a Monostable Multivibrator using IC 555 timer and explain its operation.

Ans. Text book –II , Article 8.3

Q.9 a. Explain the basic technique used for DAC.

Ans. Text book –II , Article 10.2

b. List the features of LM 723 Voltage Regulator.

Ans. Text book –II , Article 6.4

c. As shown in Fig.1 $V_{in} = 20\text{V}$, $R = 200\Omega$ and $V_z = 12\text{V}$. If $V_{BE} = 0.65\text{V}$,

(6)

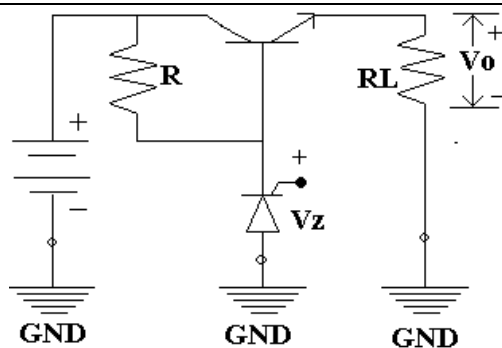


Fig.1

find

(i) V_o

(ii) The collector to emitter voltage of the pass transistor and

(iii) The current in the 200Ω resistor

C) Apply Kirchoff's voltage law around the output loop

$$V_{BE} = V_Z - V_o$$

$$\text{So } V_o = V_Z - V_{BE} = 12 - 0.065 = 11.35 \text{ V Ans}$$

$$V_{CE} = V_{in} - V_o = 20 - 11.35 = 8.65 \text{ V Ans}$$

The voltage drop across 200Ω resistance is $V_{in} = V_Z$

$$= 20 - 12 = 8 \text{ V therefore the current in resistor is } I = 8/200 = 0.04 \text{ A Ans}$$

TEXT BOOK

- I. **Electronic Devices and Circuits, Fourth Edition, David A Bell, PHI (2006)**
- II. **Linear Integrated Circuits, Revised Second Edition, D. Roy Choudhury, Shail B. Jain, New Age International Publishers**